

$$I_{R_1} = I_{R_2} = \frac{V_{DD}}{R_1 + R_2}$$

$$V_{GS} = R_2 I_{R_2} = \frac{R_2}{R_1 + R_2} V_{DD}$$

(voltage divider)

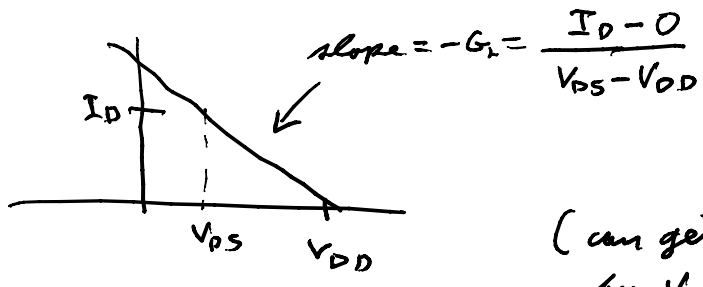
C_c = coupling capacitor

$Z_{C_c} = \frac{1}{sC_c}$ at DC (bias) $s \rightarrow 0$ or C_c opens up for bias

input on left sees R_1 & R_2 in parallel; if small R_1 , this puts a load on the input circuit on the left

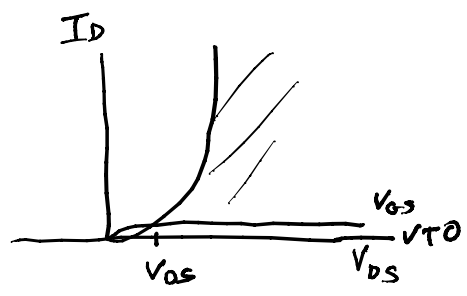
note $V_{GS} = \left(\frac{1}{1 + \frac{R_1}{R_2}}\right) V_{DD}$ so can make R_1 & R_2 large (use in MEG Ohm range)

How to adjust the gain: $|Gain| = g_m / G_L = \frac{2I_D}{V_{GS} - V_{TO}}$



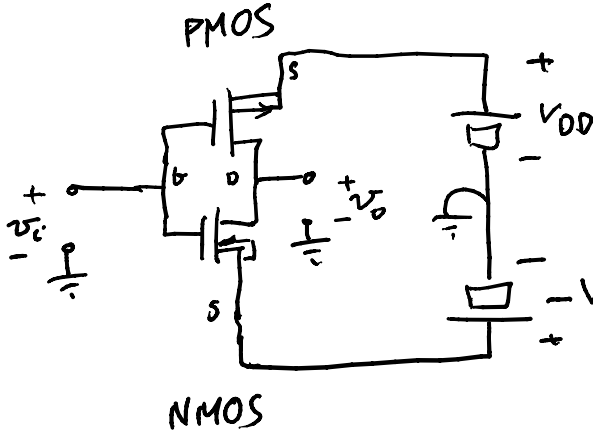
$$= 2 \left(\frac{V_{DD} - V_{DS}}{V_{GS} - V_{TO}} \right) \text{ where } V_{DS} > V_{GS} - V_{TO} \text{ (sat)}$$

(can get close to ∞ gain by $V_{DS} \rightarrow 0$ & $V_{GS} \rightarrow V_{TO}$ but decrease linearity region)

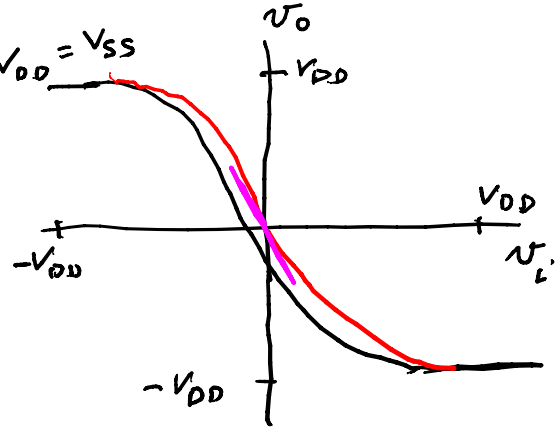


Inverter - CMOS

"complementary (N&P)"



It bias by choice of P & N to get $v_o = 0$ when $v_i = 0$



derive $v_o = 0$ when $v_i = 0$

$$V_{GS} = -V_{SG}, V_{SG} = V_{DD}; V_{SD} = V_{DD}$$

$v_i = 0$
PMOS

$$V_{GS} = V_{DD}; V_{DS} = +V_{DD}; \begin{matrix} V_{DS} \\ V_{DD} \end{matrix} > \begin{matrix} V_{GS} - V_{TO} \\ V_{DD} - V_{TO} \end{matrix} \Rightarrow \text{NMOS is in saturation}$$

\Rightarrow PMOS also in saturation

$$V_{SDP} = V_{DD} > V_{SGP} - (-V_{TOP}) = V_{DD} - |V_{TOP}|$$

$$V_{DS} < V_{GS} - V_{TO}$$

$$-I_{DP} = I_{DN}, \quad I_{DN} = \frac{K_{Pn}}{2} \left(\frac{W}{L}\right)_n (V_{GS} - V_{TO_n})^2 (1 + \lambda_n V_{DS})$$

$$-I_{DP} = \frac{K_{Pp}}{2} \left(\frac{W}{L}\right)_p (V_{SGP} - |V_{TOP}|)^2 (1 + \lambda_p V_{SDP})$$

$$\text{here can find } \left(\frac{W}{L}\right)_p = \left(\frac{W}{L}\right)_n \left(\frac{K_{Pn}}{K_{Pp}}\right) \left\{ \frac{(V_{DD} - V_{TO_n})^2 (1 + \lambda_n V_{DD})}{(V_{DD} - |V_{TOP}|)^2 (1 + \lambda_p V_{DD})} \right\}$$

allows $v_0 = 0$ when $v_i = 0$.